

Notice of References Cited

Application/Control No.

10/593,809

Applicant(s)/Patent Under
Reexamination
NARAYAN ET AL.

Examiner

JONATHAN C. LANGMAN

Art Unit

1794

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U.S. PATENT DOCUMENTS

*		Document Number	Date	Name	Classification
		Country Code-Number-Kind Code	MM-YYYY		
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	Zhang et al. ("Formation of Low Resistivity Alpha Ta by Ion Sputtering"), Journal of Vacuum Science and Technology B, Vol. 21, Issue 1, Jan/Feb 2003, pgs. 237-240.			
	V	Yuan et al. ("A New Method for Deposition of Cubic Ta Diffusion Barrier for Cu Metallization"), Thin Solid Films, Vol. 434, May 2003, pgs 126-129.			
	W	Chen et al. ("Phase Formation behavior and Diffusion Barrier Property of Reactively Sputtered Tantalum Based Thin Films used in Semiconductor Metallization"), Thin Solid Films, Vol. 353, 1999, pgs. 264-273.			
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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